

SANYO	No.4918	2SJ362
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

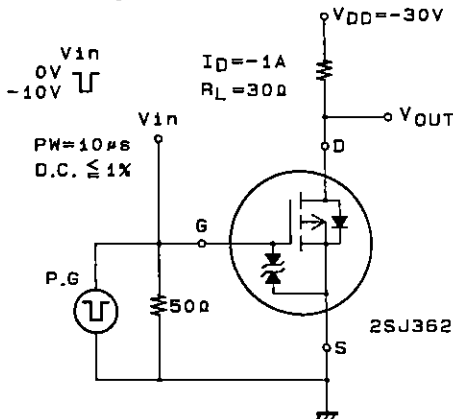
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain-to-Source Voltage	V _{DSS}	-60	V
Gate-to-Source Voltage	V _{GSS}	±25	V
Drain Current (DC)	I _D	-2	A
Drain Current (Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	A
Allowable Power Dissipation	P _D	Tc = 25°C	20 W
			1.0 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

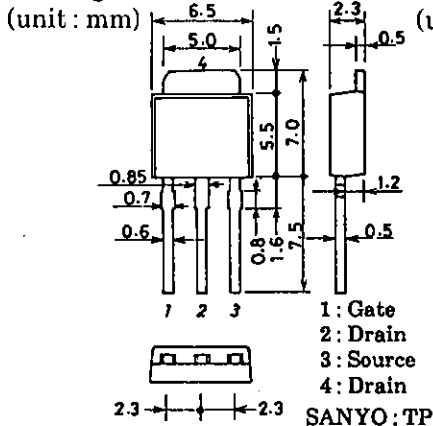
Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-60			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} = 0	±25			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60V, V _{GS} = 0			-100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0			±10	μA
Gate-to-Source Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.5		-2.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -1A	1.2	2		S
Static Drain-to-Source ON-State Resistance	R _{DSON}	I _D = -1A, V _{GS} = -10V		300	400	mΩ
	R _{DSON}	I _D = -1A, V _{GS} = -4V		450	650	mΩ
Input Capacitance	C _{iss}	V _{DS} = -20V, f = 1MHz		240		pF
Output Capacitance	C _{oss}	V _{DS} = -20V, f = 1MHz		150		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -20V, f = 1MHz		40		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		12		ns
Rise Time	t _r			16		ns
Turn-OFF Delay Time	t _{d(off)}			85		ns
Fall Time	t _f			55		ns
Diode Forward Voltage	V _{SD}	I _S = -2A, V _{GS} = 0	-1.0	-1.5		V

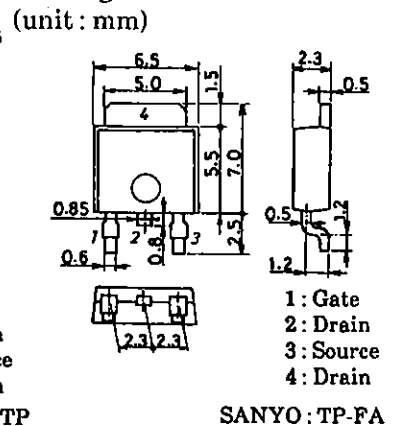
Switching Time Test Circuit

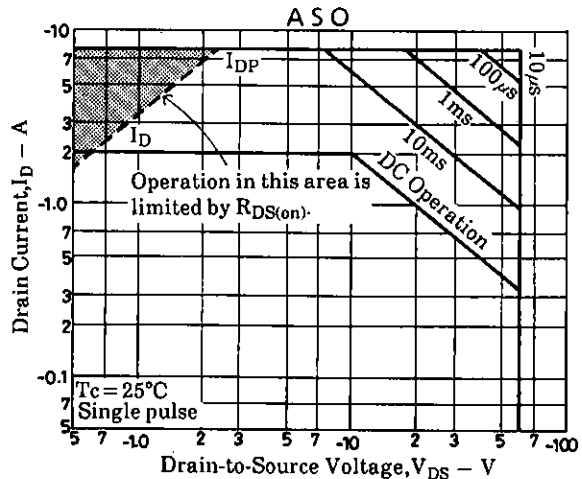
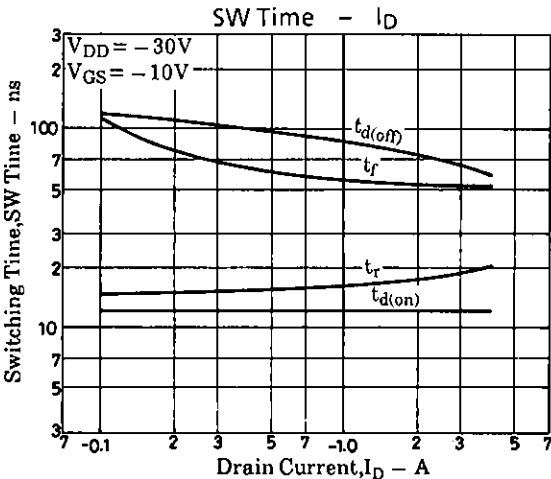
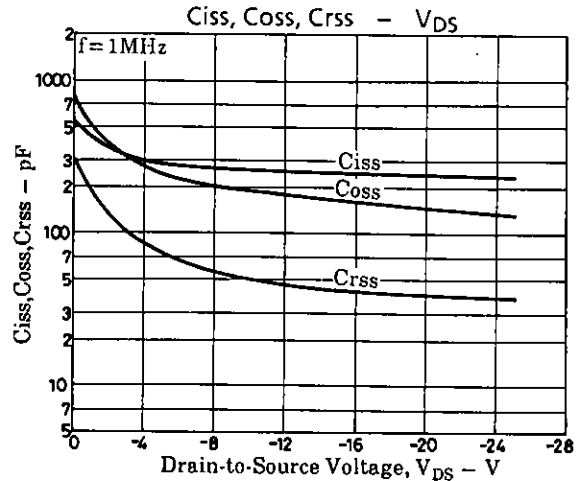
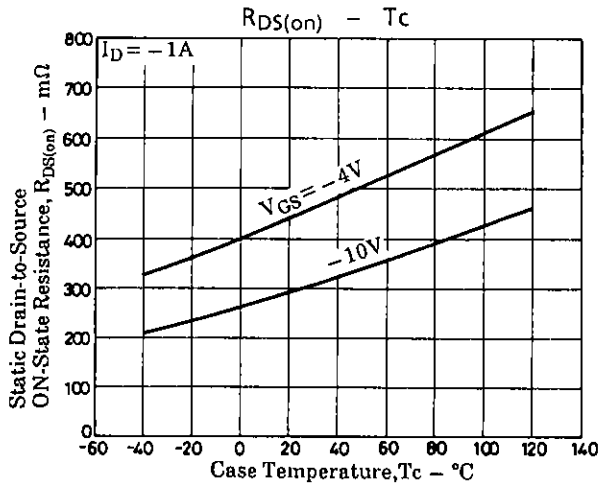
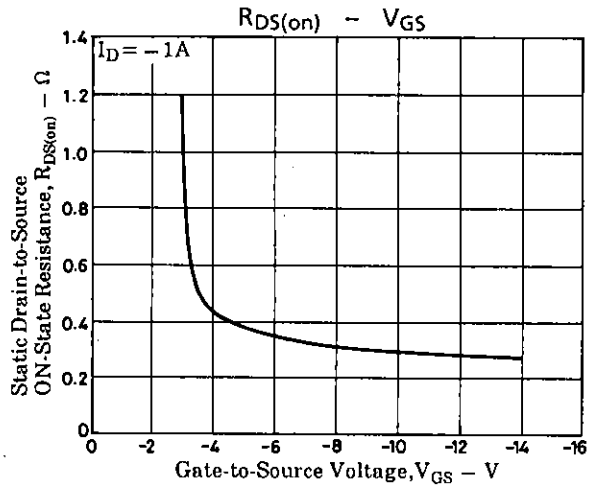
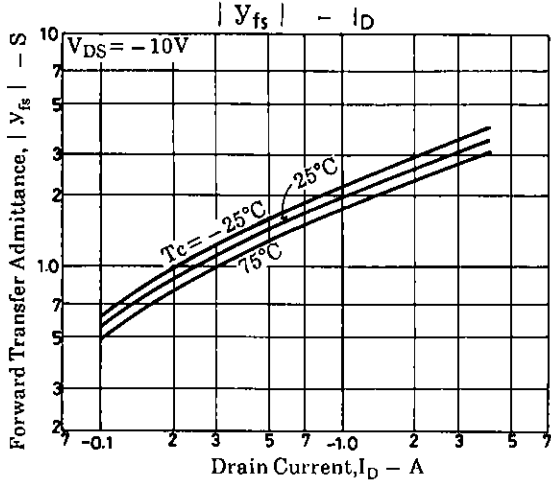
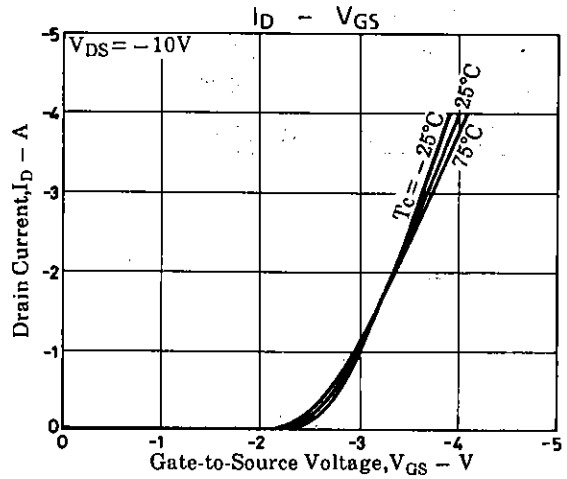
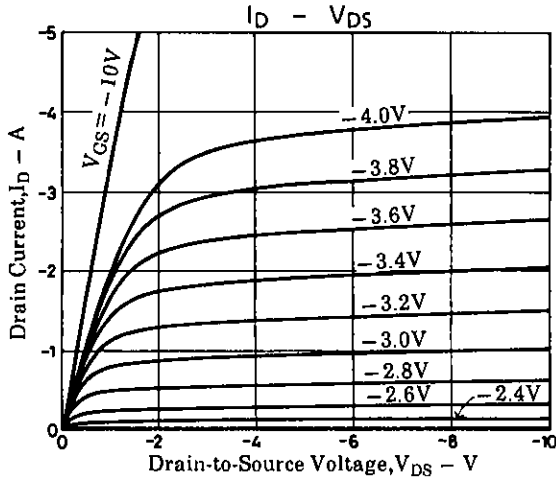


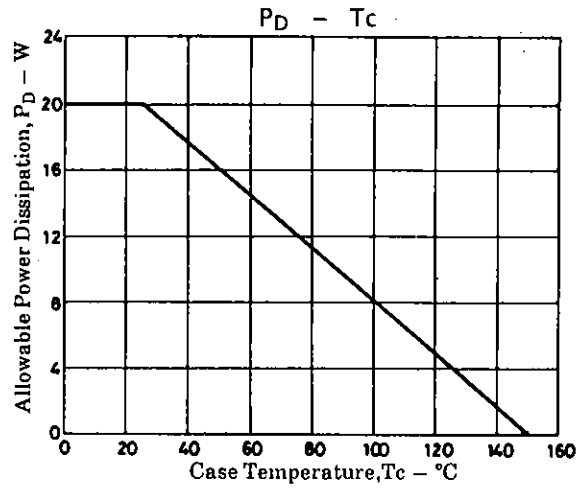
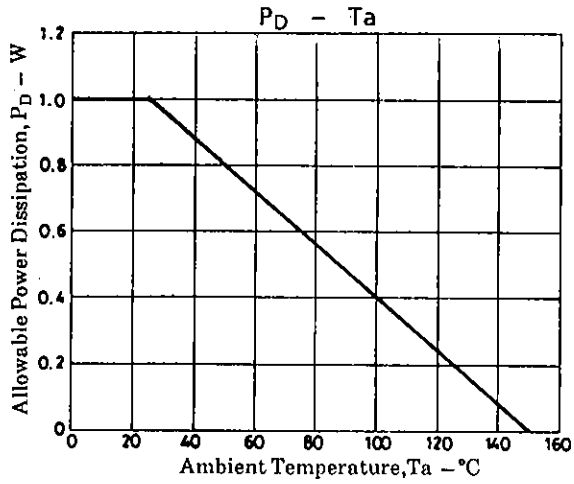
Package Dimensions 2083B



Package Dimensions 2092B







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